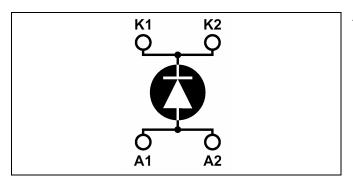


APTDF500U40G

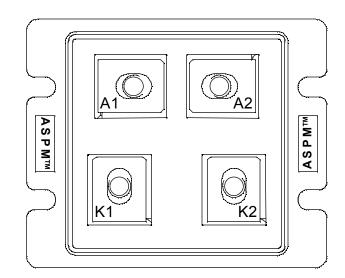
Single diode Power Module



$V_{CES} = 400V$ $I_{C} = 500A$ @ Tc = 80°C

Application

- Anti-Parallel diode
 - Switchmode Power Supply
 - Inverters
- Snubber diode
- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers
- Electric vehicles



Features

- Ultra fast recovery times
- Soft recovery characteristics
- Very low stray inductance
- High blocking voltage
- High current
- Low leakage current

Benefits

- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter			Max ratings	Unit
V _R	Maximum DC reverse Voltage			400	V
V _{RRM}	Maximum Peak Repetitive Revers	e Voltage	400	v	
т	Maximum Average Forward	During angle $= 500/$	$T_c = 25^{\circ}C$	500	
$I_{F(AV)}$	Current	Duty cycle = 50%	$T_c = 80^{\circ}C$	500	٨
I _{F(RMS)}	RMS Forward Current		850	Λ	
I _{FSM}	Non-Repetitive Forward Surge Current		$T_j = 25^{\circ}C$	5000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APTDF500U40G-Rev 1 June, 2006



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

	cal Characteristics Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{\rm F}$	Diode Forward Voltage	$I_F = 500 A$				1.5	
		$I_{\rm F} = 1000 {\rm A}$			1.5		V
		$I_F = 500 A$	$T_{j} = 150^{\circ}C$			1.3	
I _{RM}	Maximum Reverse Leakage Current	$V_{\rm R} = 400 \text{V}$ $T_{\rm j} =$	$T_j = 25^{\circ}C$			2500	
		$V_{\rm R} = 400 V$ $T_{\rm j} = 150^{\circ} C$				5000	μA
CT	Junction Capacitance	$V_R = 200 V$			800		pF

Dynamic Characteristics

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	Characteristic	Test Conditions		Min	Тур	Max	Unit	
t _{rr1}	Reverse Recovery Time	$I_F=1A, V_R=30V$ di/dt = 15A/µs	$T_j = 25^{\circ}C$			50		
t _{rr2}		$I_{\rm F} = 500 {\rm A}$	$T_j = 25^{\circ}C$			120	ns	
t _{rr3}		$V_{R} = 240V$ di/dt=1000A/µs	$T_j = 100^{\circ}C$			260		
$t_{\rm fr1}$	Forward Recovery Time		$T_j = 25^{\circ}C$		210		ns	
t _{fr2}			$T_{j} = 100^{\circ}C$		220		115	
I _{RRM1}	Reverse Recovery Current		$T_j = 25^{\circ}C$			50	Α	
I _{RRM2}			$T_{j} = 100^{\circ}C$			120		
Q _{rr1}	Reverse Recovery Charge	$I_{\rm F} = 500 {\rm A}$ $V_{\rm R} = 240 {\rm V}$	$T_j = 25^{\circ}C$			3	μC	
Q _{rr2}		$di/dt=1000A/\mu s$	$T_{j} = 100^{\circ}C$			15.6	μο	
$V_{\rm fr1}$	Forward Recovery Voltage		$T_j = 25^{\circ}C$		19		v	
V _{fr2}			$T_{j} = 100^{\circ}C$		19		•	
d _{IM/dt}	Rate of Fall of Recovery Current		$T_j = 25^{\circ}C$		1200		A/μs	
IWI/ dt			$T_{j} = 100^{\circ}C$		1800		μο	

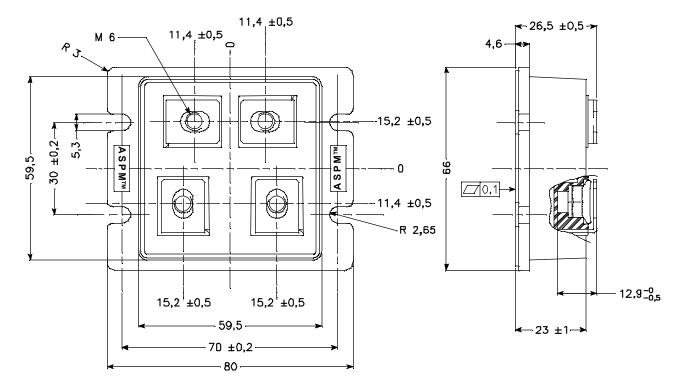
Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance					0.08	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range					125	°C
T _C	Operating Case Temperature	-40		100			
Torque	Aounting torque	To heatsink	M5	2.5		3.5	N.m
Torque	would be determined to reque	For terminals	M6	3		4	
Wt	Package Weight					250	g

APTDF500U40G-Rev 1 June, 2006



LP4 Package outline (dimensions in mm)



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.